ON Semiconductor

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Triple Buffer

NL37WZ16

The NL37WZ16 is a high performance triple buffer with inputs operating from a 1.65 V to 5.5 V supply.

Features

- Designed for 1.65 V to 5.5 V V_{CC} Operation
- 2.4 ns t_{PD} at $V_{CC} = 5 \text{ V (Typ)}$
- Inputs/Outputs Overvoltage Tolerant up to 5.5 V
- I_{OFF} Supports Partial Power Down Protection
- Source/Sink 24 mA at 3.0 V
- Available in US8, UDFN8 and UQFN8 Packages
- Chip Complexity < 100 FETs
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

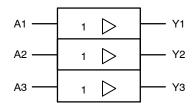


Figure 1. Logic Symbol



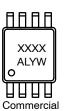
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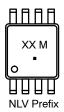
www.onsemi.com





US8 US SUFFIX CASE 493







UDFN8, 1.45x1.0 MU3 SUFFIX CASE 517BZ





UDFN8, 1.95x1.0 MU1 SUFFIX CASE 517CA





UQFN8, 1.4x1.2 MQ2 SUFFIX CASE 523AS





UQFN8, 1.6x1.6 MQ1 SUFFIX CASE 523AN



 $\begin{array}{lll} X,\, XX,\, XXXX &= \text{Specific Device Code} \\ A &= \text{Assembly Location} \\ L &= \text{Lot Code} \\ Y &= \text{Year Code} \end{array}$

Y = Year Code
W = Week Code
M = Date Code
■ = Pb-Free Package

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 6 of this data sheet.

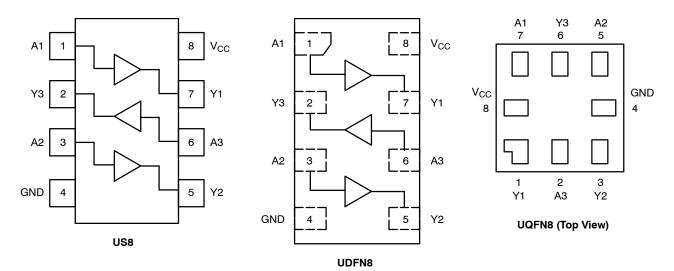


Figure 2. Pinout

PIN ASSIGNMENT

Pin	US8 / UDFN8	UQFN8
1	A1	Y1
2	Y3	А3
3	A2	Y2
4	GND	GND
5	Y2	A2
6	А3	Y3
7	Y1	A1
8	V _{CC}	V _{CC}

FUNCTION TABLE

A Input	Y Output
L	L
Н	Н

MAXIMUM RATINGS

Symbol	Chara	acteristics	Value	Unit
V _{CC}	DC Supply Voltage	NLV	-0.5 to +7.0 -0.5 to +6.5	V
V_{IN}	DC Input Voltage	NLV	-0.5 to +7.0 -0.5 to +6.5	V
V _{OUT}	DC Output Voltage (NLV)	Active-Mode (High or Low State) Tri-State Mode (Note 1) Power-Down Mode (V _{CC} = 0 V)	-0.5 to V _{CC} + 0.5 -0.5 to +7.0 -0.5 to +7.0	V
	DC Output Voltage	Active-Mode (High or Low State) Tri-State Mode (Note 1) Power-Down Mode (V _{CC} = 0 V)	-0.5 to V _{CC} + 0.5 -0.5 to +6.5 -0.5 to +6.5	V
I _{IK}	DC Input Diode Current	V _{IN} < GND	-50	mA
I _{OK}	DC Output Diode Current	V _{OUT} < GND	-50	mA
I _{OUT}	DC Output Source/Sink Current		±50	mA
I _{CC} or I _{GND}	DC Supply Current per Supply Pin or	Ground Pin	±100	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
TL	Lead Temperature, 1 mm from Case f	or 10 secs	260	°C
TJ	Junction Temperature Under Bias		+150	°C
$\theta_{\sf JA}$	Thermal Resistance (Note 2)	US8 UQFN8 UDFN8	250 210 231	°C/W
P _D	Power Dissipation in Still Air	US8 UQFN8 UDFN8	500 595 541	mW
MSL	Moisture Sensitivity		Level 1	-
F _R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	-
V _{ESD}	ESD Withstand Voltage (Note 3)	Human Body Model Charged Device Model	2000 1000	V
I _{Latchup}	Latchup Performance (Note 4)		±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Applicable to devices with outputs that may be tri-stated.
- Applicable to devices with outputs that may be the stated.
 Measured with minimum pad spacing on an FR4 board, using 10mm-by-1inch, 2 ounce copper trace no air flow per JESD51-7.
 HBM tested to ANSI/ESDA/JEDEC JS-001-2017. CDM tested to EIA/JESD22-C101-F. JEDEC recommends that ESD qualification to EIA/JESD22–A115–A (Machine Model) be discontinued per JEDEC/JEP172A.

 4. Tested to EIA/JESD78 Class II.

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics		Min	Max	Unit
V _{CC}	Positive DC Supply Voltage		1.65	5.5	V
V _{IN}	DC Input Voltage		0	5.5	V
V _{OUT}	DC Output Voltage	Active–Mode (High or Low State) Tri–State Mode (Note 1) Power–Down Mode (V_{CC} = 0 V)	0 0 0	V _{CC} 5.5 5.5	
T _A	Operating Temperature Range		-55	+125	°C
t _r , t _f	Input Rise and Fall Time (NLV)	V_{CC} = 3.0 V to 3.6 V V_{CC} = 4.5 V to 5.5 V	0 0	100 20	ns/V
	Input Rise and Fall Time	$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$ $V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$ $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$ $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	0 0 0 0	20 20 10 5	

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

			V _{CC}	T,	4 = 25°C	2	-55°C ≤ T	_A ≤ 125°C	
Symbol	Parameter	Condition	(V)	Min	Тур	Max	Min	Max	Units
V _{IH}	High-Level Input		1.65 to 1.95	0.65 V _{CC}	_	_	0.65 V _{CC}	-	٧
	Voltage		2.3 to 5.5	0.70 V _{CC}	_	-	0.70 V _{CC}	-	
V_{IL}	Low-Level Input		1.65 to 1.95	-	-	0.35 V _{CC}	-	0.35 V _{CC}	V
	Voltage		2.3 to 5.5	-	-	0.30 V _{CC}	-	0.30 V _{CC}	
V _{ОН}	High-Level Output Voltage	$\begin{split} V_{IN} &= V_{IH} \text{ or } V_{IL} \\ I_{OH} &= -100 \mu\text{A} \\ I_{OH} &= -4 \text{ mA} \\ I_{OH} &= -8 \text{ mA} \\ I_{OH} &= -12 \text{ mA} \\ I_{OH} &= -16 \text{ mA} \\ I_{OH} &= -24 \text{ mA} \\ I_{OH} &= -32 \text{ mA} \end{split}$	1.65 to 5.5 1.65 2.3 2.7 3.0 3.0 4.5	V _{CC} - 0.1 1.29 1.9 2.2 2.4 2.3 3.8	V _{CC} 1.4 2.1 2.4 2.7 2.5 4.0	- - - - -	V _{CC} - 0.1 1.29 1.9 2.2 2.4 2.3 3.8	- - - - -	٧
V _{OL}	Low-Level Output Voltage	$\begin{split} V_{IN} &= V_{IH} \text{ or } V_{IL} \\ I_{OL} &= 100 \mu\text{A} \\ I_{OL} &= 4 \text{ mA} \\ I_{OL} &= 8 \text{ mA} \\ I_{OL} &= 12 \text{ mA} \\ I_{OL} &= 16 \text{ mA} \\ I_{OL} &= 24 \text{ mA} \\ I_{OL} &= 32 \text{ mA} \end{split}$	1.65 to 5.5 1.65 2.3 2.7 3.0 3.0 4.5		- 0.08 0.2 0.22 0.28 0.38 0.42	0.1 0.24 0.3 0.4 0.4 0.55 0.55		0.1 0.24 0.3 0.4 0.4 0.55 0.55	٧
I _{IN}	Input Leakage Current	V _{IN} = 5.5 V or GND	1.65 to 5.5	-	-	±0.1	-	±1.0	μΑ
I _{OFF}	Power Off Leakage Current	V _{IN} = 5.5 V or V _{OUT} = 5.5 V	0	-	_	1.0	-	10	μΑ
I _{CC}	Quiescent Supply Current	V _{IN} = V _{CC} or GND	5.5	-	_	1.0	-	10	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS

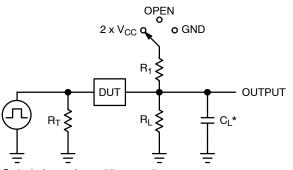
				1	_A = 25°C	;	T _A = -55	to 125°C	
Symbol	Parameter	V _{CC} (V)	Test Conditions	Min	Тур	Max	Min	Max	Units
t _{PLH} ,	Propagation Delay	1.8 ± 0.15	C _L = 15 pF	1	6.0	7.9	-	8.8	ns
t _{PHL}		2.5 ± 0.2	$R_D = 1 M\Omega$ $R_1 = Open$	1	3.0	5.2	_	5.8	
		3.3 ± 0.3		-	2.3	3.6	-	4.0	
		5.0 ± 0.5		-	1.8	2.9	_	3.2	
		3.3 ± 0.3	C _L = 50 pF,	1	3.0	4.6	_	5.1	
		5.0 ± 0.5	$R_D = 500 \Omega$, $R_1 = Open$	-	2.4	3.8	-	4.2	

^{5.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}/2 (per flip-flop). C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Units
C _{IN}	Input Capacitance	$V_{CC} = 5.5 \text{ V}, V_{IN} = 0 \text{ V or } V_{CC}$	2.5	pF
C _{OUT}	Output Capacitance	V _{CC} = 5.5 V, V _{IN} = 0 V or V _{CC}	2.5	pF
C _{PD}	Power Dissipation Capacitance (Note 6)	10 MHz, V_{CC} = 3.3 V, V_{IN} = 0 V or V_{CC} 10 MHz, V_{CC} = 5.5 V, V_{IN} = 0 V or V_{CC}	9 11	pF

^{6.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.



Test	Switch Position	C _L , pF	R_L , Ω	R ₁ , Ω
t _{PLH} / t _{PHL}	Open	See AC Character	istics Tal	ole
t _{PLZ} / t _{PZL}	2 x V _{CC}	50	500	500
t _{PHZ} / t _{PZH}	GND	50	500	500

X = Don't Care

 C_L includes probe and jig capacitance R_T is Z_{OUT} of pulse generator (typically 50 $\Omega)$

f = 1 MHz

Figure 3. Test Circuit

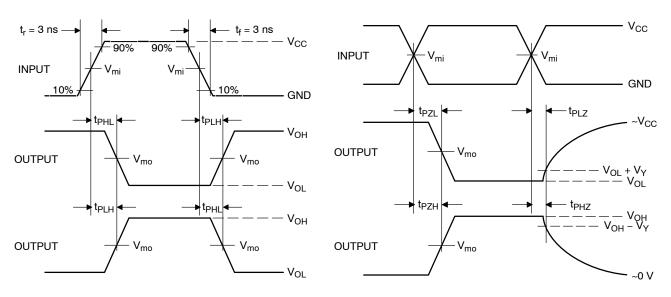


Figure 4. Switching Waveforms

		V _{mo} , V		
V _{CC} , V	V _{mi} , V	t _{PLH} , t _{PHL}	t _{PZL} , t _{PLZ} , t _{PZH} , t _{PHZ}	V _Y , V
1.65 to 1.95	V _{CC} /2	V _{CC} /2	V _{CC} /2	0.15
2.3 to 2.7	V _{CC} /2	V _{CC} /2	V _{CC} /2	0.15
3.0 to 3.6	V _{CC} /2	V _{CC} /2	V _{CC} /2	0.3
4.5 to 5.5	V _{CC} /2	V _{CC} /2	V _{CC} /2	0.3

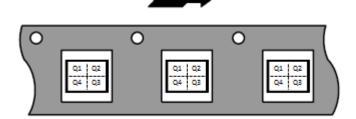
DEVICE ORDERING INFORMATION

Device	Packages	Specific Device Code	Pin 1 Orientation (See below)	Shipping [†]
NL37WZ16USG	US8	LR	Q4	3000 / Tape & Reel
NLV37WZ16USG*	US8	LR	Q4	3000 / Tape & Reel
NL37WZ16MQ1TCG (In Development)	UQFN8, 1.6 x 1.6, 0.5P	TBD	TBD	3000 / Tape & Reel
NL37WZ16MU1TCG (In Development)	UDFN8, 1.95 x 1.0, 0.5P	AC	Q4	3000 / Tape & Reel
NL37WZ16MU2TCG (In Development)	UDFN8, 1.6 x 1.0, 0.4P	AE	Q4	3000 / Tape & Reel
NL37WZ16MU3TCG (In Development)	UDFN8, 1.45 x 1.0, 0.35P	E	Q4	3000 / Tape & Reel
NL37WZ16MQ2TCG (In Development)	UQFN8, 1.4 x 1.2, 0.4P	TBD	TBD	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

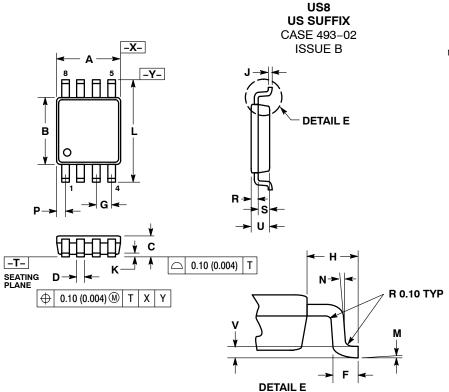
Pin 1 Orientation in Tape and Reel

Direction of Feed



^{*}NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

PACKAGE DIMENSIONS

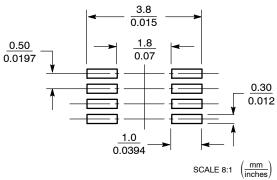


- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. DIMENSION "A" DOES NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURR. MOLD FLASH. PROTRUSION AND GATE BURR SHALL NOT EXCEED 0.140 MM (0.0055") PER SIDE.
 4. DIMENSION "B" DOES NOT INCLUDE INTER-LEAD FLASH OR PROTRUSION. INTER-LEAD FLASH AND PROTRUSION SHALL NOT E3XCEED 0.140 (0.0055") PER SHALL NOT E3XCEED 0.140 (0.0055") PER
- SIDE.

 5. LEAD FINISH IS SOLDER PLATING WITH THICKNESS OF 0.0076–0.0203 MM.
- (300-800 "). 6. ALL TOLERANCE UNLESS OTHERWISE SPECIFIED ±0.0508 (0.0002 ").

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	1.90	2.10	0.075	0.083	
В	2.20	2.40	0.087	0.094	
С	0.60	0.90	0.024	0.035	
D	0.17	0.25	0.007	0.010	
F	0.20	0.35	0.008	0.014	
G	0.50	BSC	0.020 BSC		
Н	0.40	REF	0.016	REF	
J	0.10	0.18	0.004	0.007	
K	0.00	0.10	0.000	0.004	
L	3.00	3.20	0.118	0.126	
М	0 °	6°	0 °	6°	
N	5 °	10 °	5 °	10 °	
P	0.23	0.34	0.010	0.013	
R	0.23	0.33	0.009	0.013	
S	0.37	0.47	0.015	0.019	
U	0.60	0.80	0.024	0.031	
V	0.12	BSC	0.005	BSC	

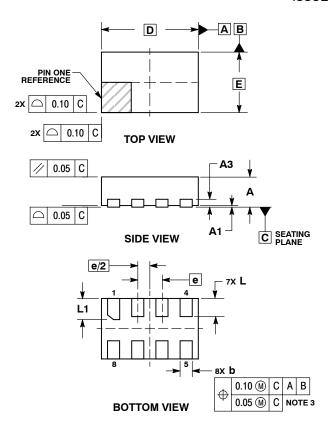
SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

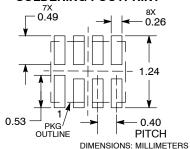
UDFN8, 1.6x1, 0.4P CASE 517BY ISSUE O



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20 MM FROM TERMINAL TIP.
 4. PACKAGE DIMENSIONS EXCLUSIVE OF BURRS AND MOLD FLASH.

	MILLIMETERS		
DIM	MIN	MAX	
Α	0.45	0.55	
A1	0.00	0.05	
А3	0.13	REF	
b	0.15	0.25	
D	1.60	BSC	
Е	1.00	BSC	
е	0.40	BSC	
Ĺ	0.25	0.35	
11	0.30	0.40	

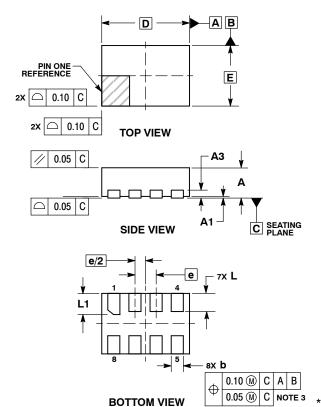
RECOMMENDED SOLDERING FOOTPRINT*



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PACKAGE DIMENSIONS

UDFN8, 1.45x1, 0.35P CASE 517BZ ISSUE O



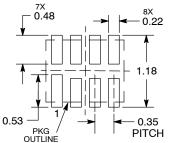
- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
- ASME Y14.5M, 1994.

 2. CONTROLLING DIMENSION: MILLIMETERS.

 3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN
- 0.15 AND 0.20 MM FROM TERMINAL TIP. PACKAGE DIMENSIONS EXCLUSIVE OF BURRS AND MOLD FLASH.

	MILLIMETERS	
DIM	MIN	MAX
Α	0.45	0.55
A1	0.00	0.05
А3	0.13 REF	
b	0.15	0.25
D	1.45 BSC	
E	1.00 BSC	
е	0.35 BSC	
L	0.25	0.35
L1	0.30	0.40

RECOMMENDED SOLDERING FOOTPRINT*

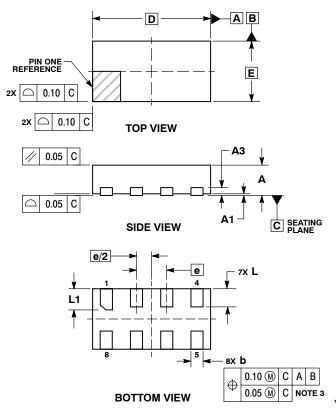


DIMENSIONS: MILLIMETERS

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PACKAGE DIMENSIONS

UDFN8, 1.95x1, 0.5P CASE 517CA ISSUE O



NOTES:

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

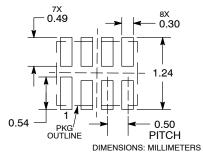
 2. CONTROLLING DIMENSION: MILLIMETERS.

 3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20 MM FROM TERMINAL TIP.

 4. PACKAGE DIMENSIONS EXCLUSIVE OF BURRS AND MOLD FLASH.

	MILLIMETERS	
DIM	MIN	MAX
Α	0.45	0.55
A1	0.00	0.05
А3	0.13 REF	
b	0.15	0.25
D	1.95 BSC	
Е	1.00 BSC	
е	0.50 BSC	
L	0.25	0.35
L1	0.30	0.40

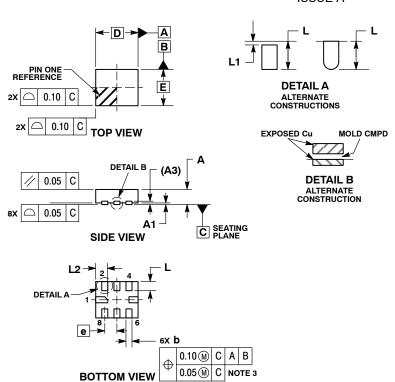
RECOMMENDED SOLDERING FOOTPRINT*



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PACKAGE DIMENSIONS

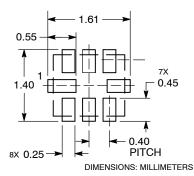
UQFN8, 1.4x1.2, 0.4P CASE 523AS **ISSUE A**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.25 mm FROM THE TERMINAL TIP.

	MILLIMETERS	
DIM	MIN	MAX
Α	0.45	0.55
A1	0.00	0.05
А3	0.13 REF	
b	0.15	0.25
D	1.40 BSC	
Е	1.20 BSC	
е	0.40 BSC	
L	0.20	0.40
L1		0.15
L2	0.30	0.50

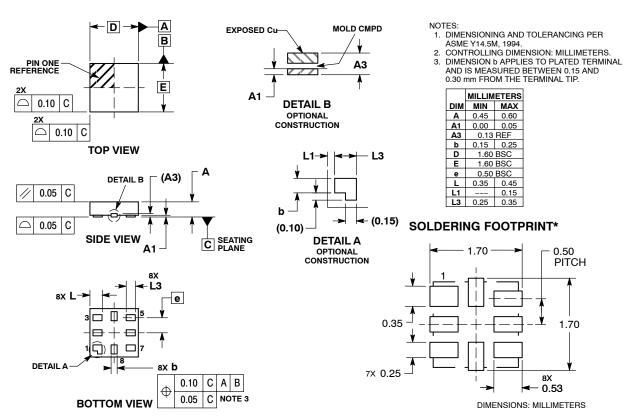
SOLDERING FOOTPRINT*



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PACKAGE DIMENSIONS

UQFN8, 1.6x1.6, 0.5P CASE 523AN ISSUE O



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